

TRANSISTOR (PNP)

Plastic-Encapsulate Transistor

FEATURES

Power dissipation

P_{CM} : 0.9W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -1A

Collector-base voltage

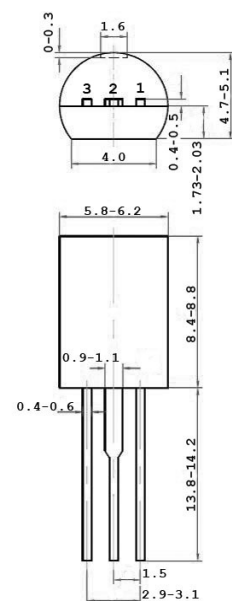
$V_{(BR)CBO}$: -160V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

TO-92MOD

1. EMITTER
2. COLLECTOR
3. BASE



UNIT:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at $25^{\circ}C$ ambient temperature unless otherwise specified.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-160		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-160		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-6		V
Collector cut-off current	I_{CBO}	$V_{CB}=-150V, I_E=0$		-1	μA
Collector cut-off current	I_{CEO}	$I_{CE}=-120V, I_B=0$		-10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-6V, I_C=0$		-1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-5V, I_C=-200mA$	65	310	
	$h_{FE(2)}$	$V_{CE}=-5V, I_C=-50mA$	40		
Collector-emitter saturation voltage	V_{CEsat}	$I_C=-500mA, I_B=-50mA$		-1.5	V
Base-emitter voltage	V_{BE}	$I_C=-5mA, I_{CE}=-5V$		-0.75	V
Transition frequency	f_r	$V_{CE}=-5V, I_C=-200mA$	15		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	R	O	Y
Range	60-120	120-200	200-300